AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

- 1. (original) Photoresist composition suitable for use at 10-165 nm comprising:
- (a) a polymeric binder
- (b) a photoactive compound
- (c) a dissolution inhibitor, the dissolution inhibitor comprising at least
 - (i) two aromatic groups,
 - (ii) fluorine and
 - (iii) a blocked acid group which when unblocked has a pKa < 12.
- 2. (original) Photoresist composition according to claim 1 wherein the photoresist composition generally will contain:
 - (a) about 50 to about 99.5 wt% polymeric binder
 - (b) about 0 to about 10 wt% photoactive compound
- (c) about 0.5 to about 50 wt% dissolution inhibitor relative to the total (a) + (b) + (c).
- 3. (currently amended) Photoresist composition according to any one of claims 1-2 claim 1 wherein the composition has an absorption coefficient of less than about 3 µm⁻¹.
- 4. (currently amended) Photoresist composition according to any one of claims
 1-3 claim 1 wherein the dissolution inhibitor, when used at 10 wt% in a polymeric binder adds about 0.8 μm⁻¹ or less to the absorbance coefficient of the composition.
- 5. (currently amended) Photoresist composition according to any one of claims 1-4 claim 1 wherein the dissolution inhibitor has 2-5 aromatic atoms.

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- 6. (currently amended) Photoresist according to any one of claims 1-5 claim 1 wherein the dissolution inhibitor has 2 or more fluorine atoms.
- 7. (currently amended) Photoresist according to any one of claims 1-6 claim 1 wherein the acid group is an hydroxyl group bound to an aromatic group, or a C(CF₃)₂OH bound to an aromatic ring.
- 8. (currently amended) Photoresist according to any one of claims 1-7 claim 1 wherein the acid group is at least partly blocked with a carbonate, acetal group, ortho ester, or tertiary alkyl group.
- 9. (currently amended) Photoresist according to any one of claims 1-8 claim 1 wherein the dissolution inhibitor comprises a bisphenol structure.
 - 10. (original) Compounds represented by formula 1[[.]]

in which n = 1-4

at least on of R^1 - R^{10} independently comprise a (blocked) acid group, the group when unblocked has a pKa < 12[[.]],

the other R¹-R¹⁰ represent independently hydrogen, fluorine or hydrocarbonaceous substituents[[.]],

R¹¹ is an aliphatic fluorinated group[[.]],

R¹² represents hydrogen or an aliphatic group having 1-10 carbon atoms and 0-13 fluorine atoms,

and R11 and R12 are not both CF3.

- 11. (original) Compound according to claim 10 wherein R¹¹ preferably is a C₂-C₁₀ group, having 2-20 fluorine atoms.
- 12. (currently amended) Compound according to any one of claims 10-11 claim 10 wherein one of {R¹-R³, R⁹, R¹⁰} and one of R⁴-R⁸, independently, are preferably hydroxy or C(CF₃)₂OH, any of these optionally protected with an acid labile protecting group.
- 13. (currently amended) Compound according to any one of claims 10-12 claim 10 wherein the other R¹-R¹⁰ independently, are hydrogen.
- 14. (currently amended) Compound according to any one of claims 10-13 claim 10 wherein R¹² preferably is hydrogen.
- 15. (currently amended) Process for forming an etched layer in a chip comprisis comprises, in order:
- (A) forming a photoresist layer on a substrate wherein the photoresist layer is prepared from a photoresist composition comprising:
 - (a) a binder;
 - (b) a photoactive component; and
- (c) the at least one dissolution inhibitor, the dissolution inhibitor comprising at least (i) two aromatic groups (ii) fluorine, and (iii) a (blocked) acid group which when unblocked has a pKa < 12
- (B) imagewise exposing a photoresist layer to form imaged and non-imaged areas,
- (C) developing the exposed photoresist layer having imaged and non- imaged areas to form the relief image on the substrate
 - (D) etching the substrate to a predetermined depth
 - (E) removing the relief image from the substrate.

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- 16. (currently amended) A process for the production of a chip by using immersion lithography, comprising the step of forming a photoresist layer on a substrate, wherein the photoresist layer is prepared from a photoresist composition comprising:
 - (a) a binder;
 - (b) a photoactive component[[.]];
 - (c) a fluor containing compound.